



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

- V_{DS} 60V
- I_D 12A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) 8.5 mohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) 12 mohm
- 100% EAS Tested

YJS12G06D



Typical Performance Characteristics

Figure1. Output Characteristics

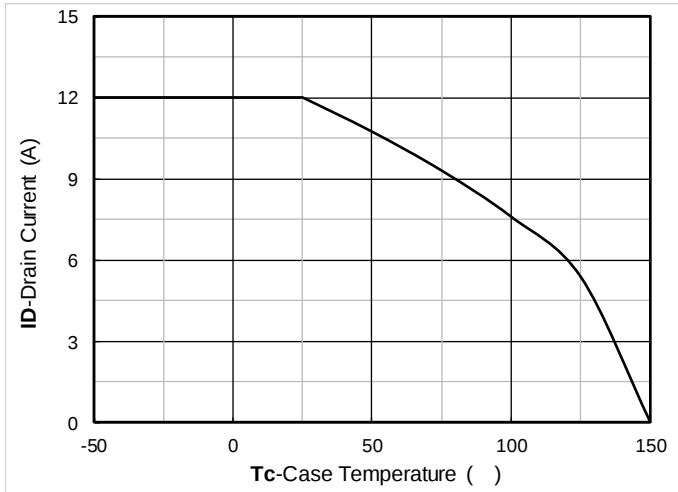


Figure7. Drain current

Figure8. Safe Operation Area

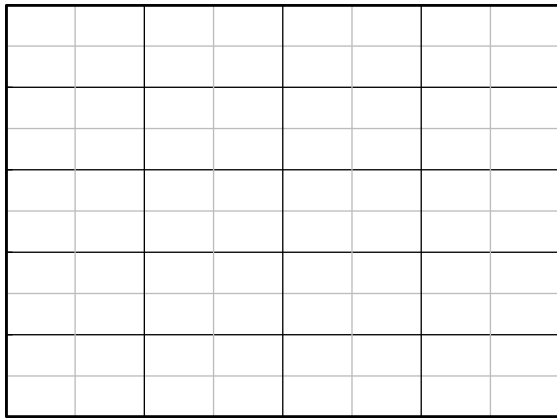


Figure 9. On-Resistance vs Gate to Source Voltage

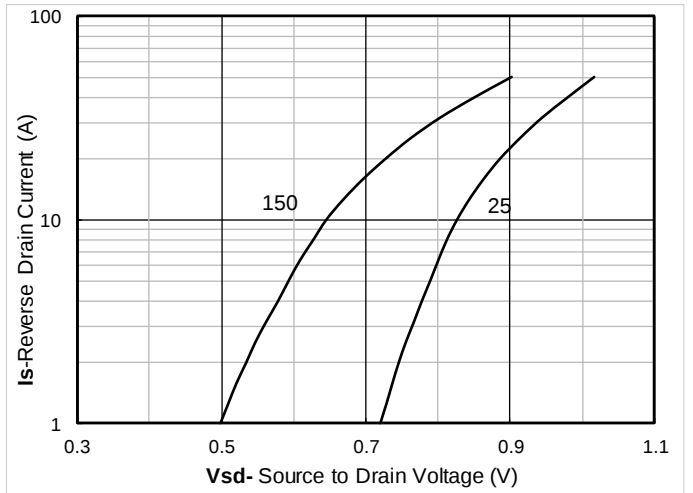


Figure 10. Forward characteristics of reverse diode

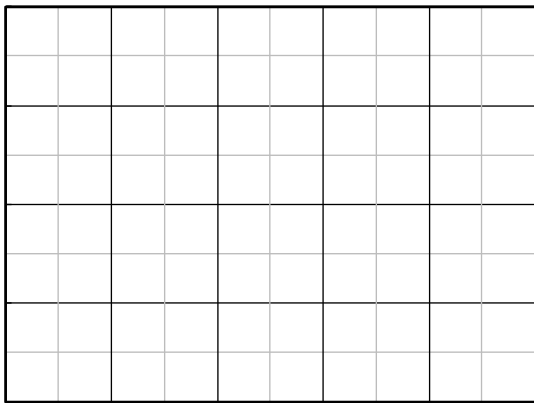


Figure 11. Normalized breakdown voltage

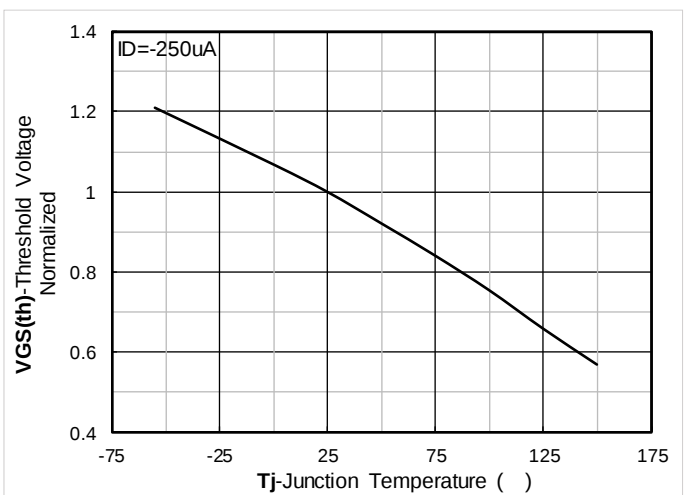


Figure 1



Figure

